

MD7003,A,B,F,AF MQ7003

MD7003,A,B
CASE 654-07, STYLE 1

MD7003F,AF
CASE 610A-04, STYLE 1

MQ7003
CASE 607-04, STYLE 1

DUAL
AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3810 for curves.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit		
Collector-Emitter Voltage	V _{CEO}	40	Vdc		
Collector-Base Voltage	V _{CBO}	50	Vdc		
Emitter-Base Voltage	V _{EBO}	5.0	Vdc		
Collector Current — Continuous	I _C	50	mAdc		
		One Die	All Die Equal Power		
Total Device Dissipation @ T _A = 25°C	P _D			mW	
		MD7003,A,B	550		600
		MD7003F,AF	350		400
		MQ7003	400		600
		Derate above 25°C			
MD7003,A,B	3.14	3.42			
MD7003F,AF	2.0	2.28			
MQ7003	2.28	3.42			
Total Device Dissipation @ T _C = 25°C	P _D			Watts	
		MD7003,A,B	1.4		2.0
		MD7003F,AF	0.7		1.4
		MQ7003	0.7		2.8
		Derate above 25°C			
MD7003,A,B	8.0	11.4			
MD7003F,AF	4.0	8.0			
MQ7003	4.0	16			
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C		

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit	
Thermal Resistance, Junction to Case	R _{θJC}			°C/W	
		MD7003,A,B	125		87.5
		MD7003F,AF	250		125
		MQ7003	250		62.6
Thermal Resistance, Junction to Ambient	R _{θJA} (1)			°C/W	
		MD7003,A,B	319		292
		MD7003F,AF	500		438
		MQ7003	438		292
Coupling Factor		Junction to Ambient	Junction to Case	%	
		MD7003,A,B	83		40
		MD7003F,AF	75		0
		MQ7003 (Q1-Q2)	57		0
		(Q1-Q3 or Q1-Q4)	55		0

(1) R_{θJA} is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	40	—	—	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	—	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	I _{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(2) (I _C = 100 μAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc)	h _{FE}	40	350	—	—
		50	350	—	—

MD7003,A,B,F,AF, MQ7003

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{CE(sat)}$	—	0.25	0.35	Vdc
Base-Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{BE(sat)}$	—	0.6	1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 5.0\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	200	300	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 100\text{ kHz}$)	C_{obo}	—	3.0	6.0	pF
Input Capacitance ($V_{BE} = 2.0\text{ Vdc}$, $I_C = 0$, $f = 100\text{ kHz}$)	C_{ibo}	—	2.0	8.0	pF
Noise Figure ($I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 10\text{ Vdc}$, $R_S = 3.0\text{ kohms}$, $f = 10\text{ Hz}$ to 15.7 kHz)	NF	—	2.0	—	dB

MATCHING CHARACTERISTICS

DC Current Gain Ratio(3) ($I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 10\text{ Vdc}$)	MD7003A,AF MD7003B	h_{FE1}/h_{FE2}	0.75 0.85	— —	1.0 1.0	—
Base-Emitter Voltage Differential ($I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 10\text{ Vdc}$)	MD7003A,AF MD7003B	$ V_{BE1} - V_{BE2} $	— —	— —	25 15	mV

(2) Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

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